

CLAIM AMENDMENTS

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claim 1 (previously presented). A susceptor for supporting a semiconductor wafer having a diameter of at least 300mm and a perimeter edge, the susceptor comprising:

a surface for supporting the semiconductor wafer, said surface having a concave shaped surface area, said surface area being configured to cause the semiconductor wafer to contact said surface area at the perimeter edge only, said surface having a center portion and an outer portion surrounding said center portion, defining a distance between said center portion and a plane defined by a circle along said outer portion, said circle having a diameter of substantially 300mm and said distance being greater than 500 μ m; and

a heater thermally coupled to said surface for heating said surface.

Claims 2-4 (previously canceled).

Claim 5 (original). The susceptor according to claim 1, wherein said susceptor is formed of metal.

Claim 6 (original). The susceptor according to claim 1, wherein said heater is configured to heat the wafer to a temperature of at least 400°C.

Claim 7 (canceled).

Claim 8 (original). The susceptor according to claim 1, wherein said surface is formed with a plurality of concentric, projecting rings.

Claim 9 (new). A susceptor for supporting a semiconductor wafer having a diameter of at least 300mm and a perimeter edge, the susceptor comprising:

a surface for supporting the semiconductor wafer, said surface having a concave shaped surface area, said surface area being configured to cause the semiconductor wafer to constantly contact said surface area at the perimeter edge only, said surface having a center portion and an outer portion surrounding said center portion, defining a distance between said center portion and a plane defined by a circle along said

outer portion, said circle having a diameter of substantially 300mm and said distance being substantially 500 μ m; and a heater thermally coupled to said surface for heating said surface.

Claim 10 (new). The susceptor according to claim 9, wherein said distance is 500 μ m.

Claim 11 (new). The susceptor according to claim 1, wherein said semiconductor wafer is constantly in contact with said surface area at the perimeter edge only for thermal contact between said wafer and said surface area.